

# High Voltage Thyristor \ Diode Module

$$V_{RRM} = 2 \times 2200 \text{ V}$$

$$I_{TAV} = 180 \text{ A}$$

$$V_T = 1.18 \text{ V}$$

Phase leg

Part number

**MCNA180PD2200YB**



Backside: isolated

 E72873



## Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability

## Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

## Package: Y4

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

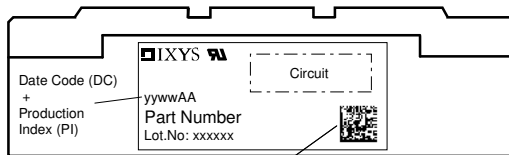
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Rectifier			Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage				2300	V	
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage				2200	V	
$I_{RD}$	reverse current, drain current	$V_{R/D} = 2200\text{ V}$			400	$\mu\text{A}$	
		$V_{R/D} = 2200\text{ V}$			30	mA	
$V_T$	forward voltage drop	$I_T = 180\text{ A}$			1.24	V	
		$I_T = 360\text{ A}$			1.49	V	
		$I_T = 180\text{ A}$	$T_{VJ} = 125^\circ\text{C}$			1.18	V
		$I_T = 360\text{ A}$	$T_{VJ} = 125^\circ\text{C}$			1.51	V
$I_{TAV}$	average forward current	$T_C = 85^\circ\text{C}$			180	A	
$I_{T(RMS)}$	RMS forward current	180° sine			280	A	
$V_{T0}$	threshold voltage	} for power loss calculation only			0.85	V	
$r_T$	slope resistance				1.8	m $\Omega$	
$R_{thJC}$	thermal resistance junction to case				0.17	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.09		K/W	
$P_{tot}$	total power dissipation		$T_C = 25^\circ\text{C}$		675	W	
$I_{TSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		5.40	kA	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		5.83	kA	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^\circ\text{C}$		4.59	kA	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		4.96	kA	
$I^2t$	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^\circ\text{C}$		145.8	kA <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		141.4	kA <sup>2</sup> s	
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 140^\circ\text{C}$		105.3	kA <sup>2</sup> s	
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$		102.1	kA <sup>2</sup> s	
$C_J$	junction capacitance	$V_R = 700\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		146	pF	
$P_{GM}$	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 140^\circ\text{C}$		120	W	
		$t_p = 300\text{ }\mu\text{s}$			60	W	
$P_{GAV}$	average gate power dissipation				8	W	
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 140^\circ\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 540\text{ A}$			150	A/ $\mu\text{s}$	
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.5\text{ A}/\mu\text{s};$ $I_G = 0.5\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 180\text{ A}$			500	A/ $\mu\text{s}$	
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ\text{C}$		1000	V/ $\mu\text{s}$	
		$R_{GK} = \infty$ ; method 1 (linear voltage rise)					
$V_{GT}$	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^\circ\text{C}$		2	V	
			$T_{VJ} = -40^\circ\text{C}$		2.6	V	
$I_{GT}$	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^\circ\text{C}$		150	mA	
			$T_{VJ} = -40^\circ\text{C}$		200	mA	
$V_{GD}$	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^\circ\text{C}$		0.2	V	
$I_{GD}$	gate non-trigger current				10	mA	
$I_L$	latching current	$t_p = 30\text{ }\mu\text{s}$	$T_{VJ} = 25^\circ\text{C}$		200	mA	
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
$I_H$	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^\circ\text{C}$		200	mA	
$t_{gd}$	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^\circ\text{C}$		2	$\mu\text{s}$	
		$I_G = 0.5\text{ A}; di_G/dt = 0.5\text{ A}/\mu\text{s}$					
$t_q$	turn-off time	$V_R = 100\text{ V}; I_T = 180\text{ A}; V = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^\circ\text{C}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$		200		$\mu\text{s}$	

Package Y4		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			300	A
$T_{VJ}$	virtual junction temperature		-40		140	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		125	°C
<b>Weight</b>				150		g
$M_D$	mounting torque		2.25		2.75	Nm
$M_T$	terminal torque		4.5		5.5	Nm
$d_{Spp/APP}$	creepage distance on surface   striking distance through air	terminal to terminal	14.0	10.0		mm
$d_{Spb/APb}$		terminal to backside	16.0	16.0		mm
$V_{ISOL}$	isolation voltage	t = 1 second		4800		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	4000		V



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

### Part description

M = Module  
 C = Thyristor (SCR)  
 N = High Voltage Thyristor  
 A = ( $\geq 2000$ V)  
 180 = Current Rating [A]  
 PD = Phase leg  
 2200 = Reverse Voltage [V]  
 YB = Y4-M6

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCNA180PD2200YB	MCNA180PD2200YB	Box	6	520502

Similar Part	Package	Voltage class
MCNA150PD2200YB	Y4-M6	2200
MCNA220PD2200YB	Y4-M6	2200

### Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 140^\circ\text{C}$

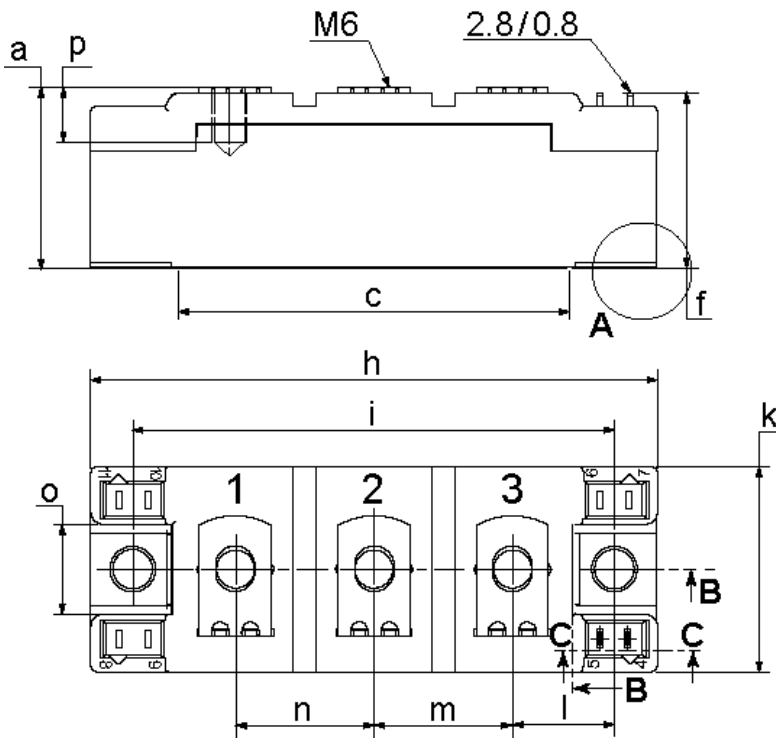


Thyristor

$V_{0\ max}$	threshold voltage	0.85	V
$R_{0\ max}$	slope resistance *	1.18	m $\Omega$

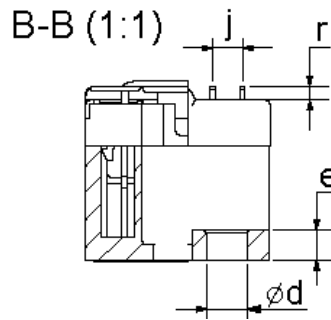


**Outlines Y4**



Dim.	MIN [mm]	MAX [mm]	MIN [inch]	MAX [inch]
a	30.0	30.6	1.181	1.205
b	typ. 0.25		typ. 0.010	
c	64.0	65.0	2.520	2.559
d	6.5	7.0	0.256	0.275
e	4.9	5.1	0.193	0.201
f	28.6	29.2	1.126	1.150
g	7.3	7.7	0.287	0.303
h	93.5	94.5	3.681	3.720
i	79.5	80.5	3.130	3.169
j	4.8	5.2	0.189	0.205
k	33.4	34.0	1.315	1.339
l	16.7	17.3	0.657	0.681
m	22.7	23.3	0.894	0.917
n	22.7	23.3	0.894	0.917
o	14.0	15.0	0.551	0.591
p	typ. 10.5		typ. 0.413	
r	1.8	2.4	0.071	0.041

Optional accessories for modules  
Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red  
Type ZY 180L (L = Left for pin pair 4/5) UL 758, style 3751



## Thyristor

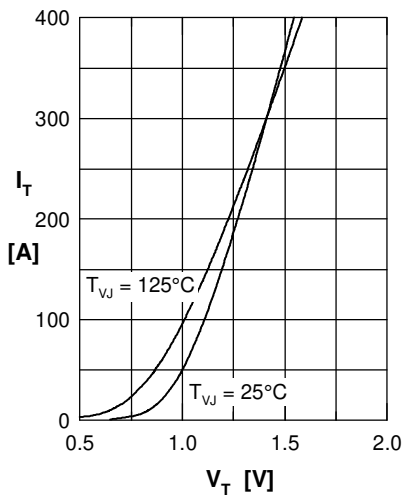


Fig. 1 Forward characteristics

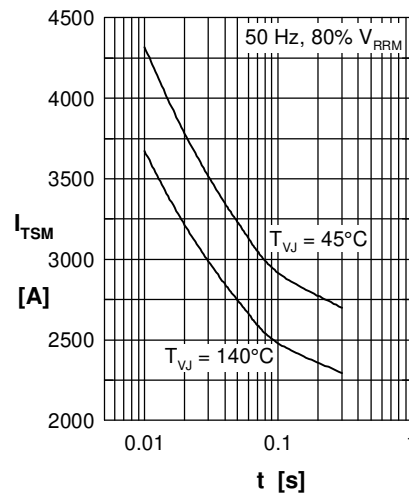


Fig. 2 Surge overload current  
 $I_{TSM}$ : crest value,  $t$ : duration

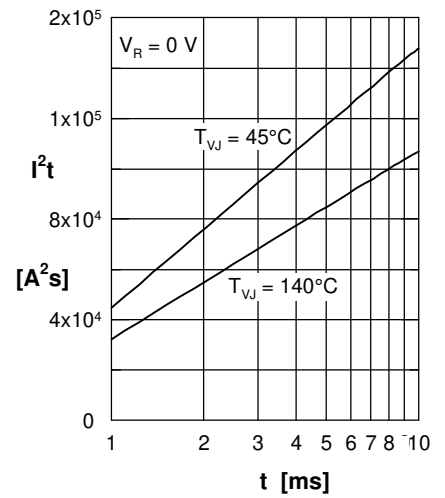


Fig. 3  $I^2t$  versus time (1-10 s)

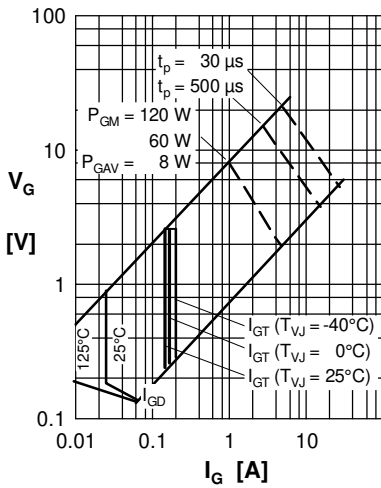


Fig. 4 Gate voltage & gate current

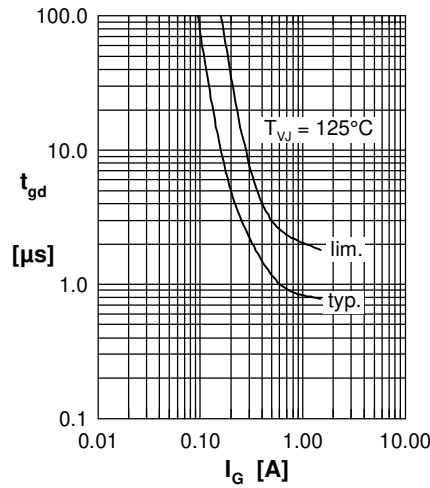


Fig. 5 Gate controlled delay time  $t_{gd}$

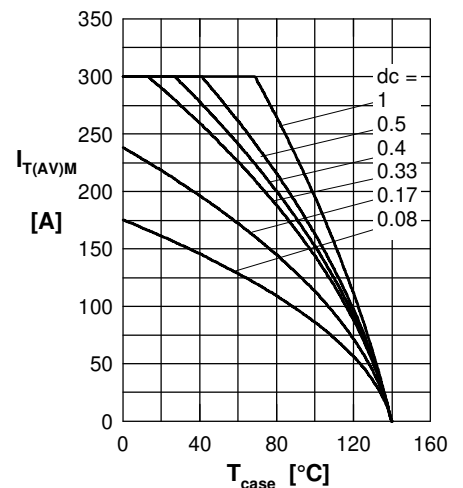


Fig. 6 Max. forward current at case temperature

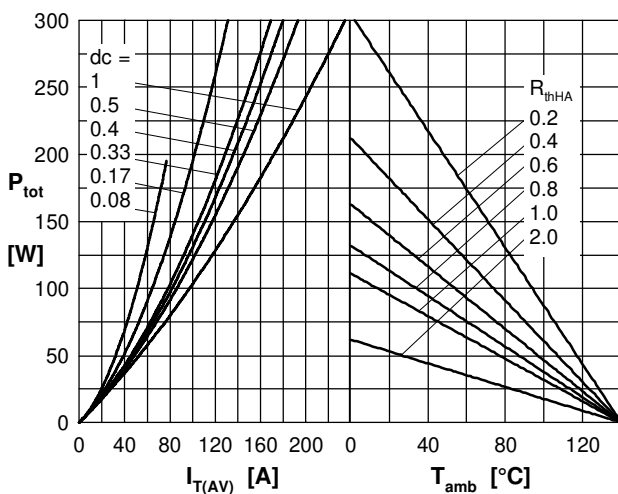


Fig. 7a Power dissipation versus direct output current  
Fig. 7b and ambient temperature

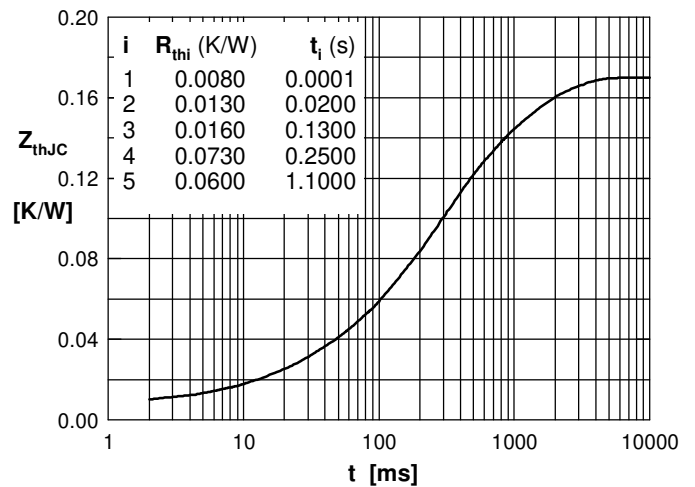


Fig. 8 Transient thermal impedance junction to case